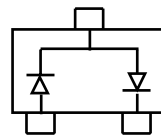
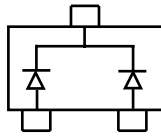
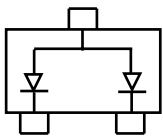
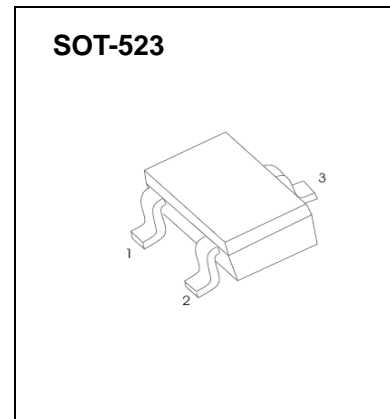


Plastic-Encapsulate Diodes

SWITCHING DIODE

FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance



BAW56T Marking: JD

BAV70T Marking: JJ

BAV99T Marking: JE

Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Reverse voltage	V_R	85	V
Forward current	I_o	75	mA
Forward power dissipation	P_D	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=1\mu A$	85		V
Reverse voltage leakage current	I_{R1}	$V_R=75V$		2	μA
	I_{R2}	$V_R=25V$		0.03	μA
Forward voltage	V_F	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R=0$ $f=1MHz$		1.5	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10mA$ $I_{tr}=0.1 \times I_R, R_L=100\Omega$		4	ns



CHINA BASE
INTERNATIONAL

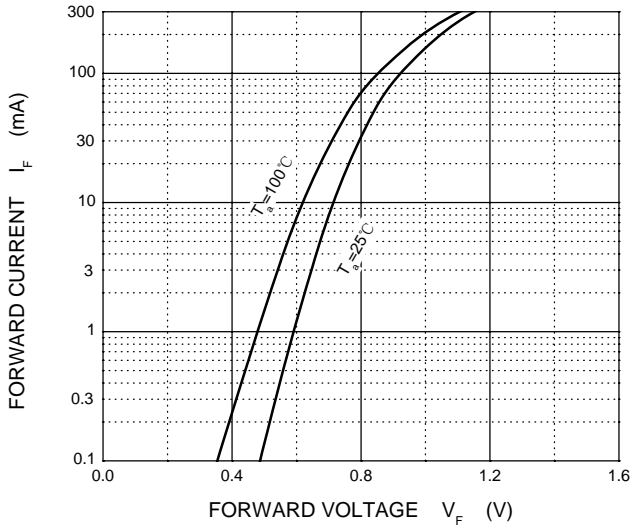
SOT-523



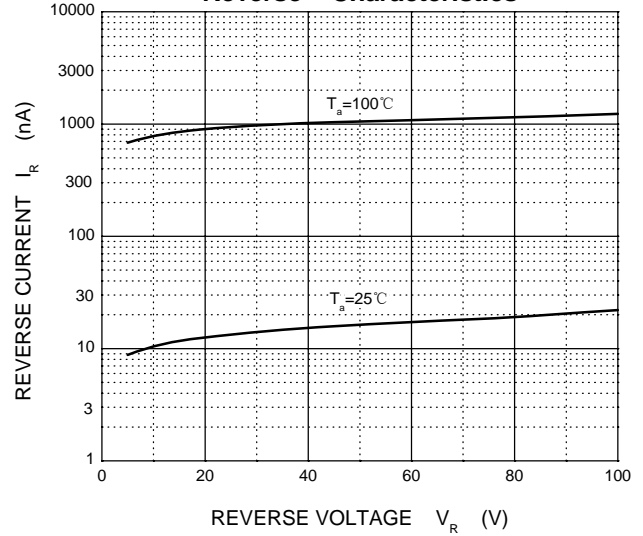
BAW56T/BAV70T/BAV99T

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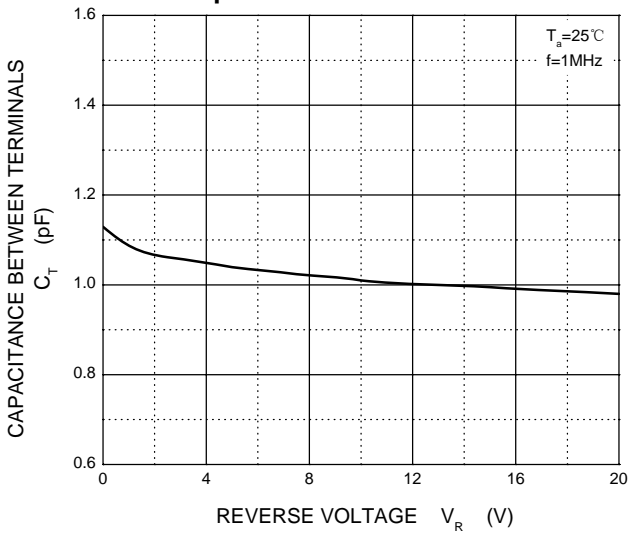
Forward Characteristics



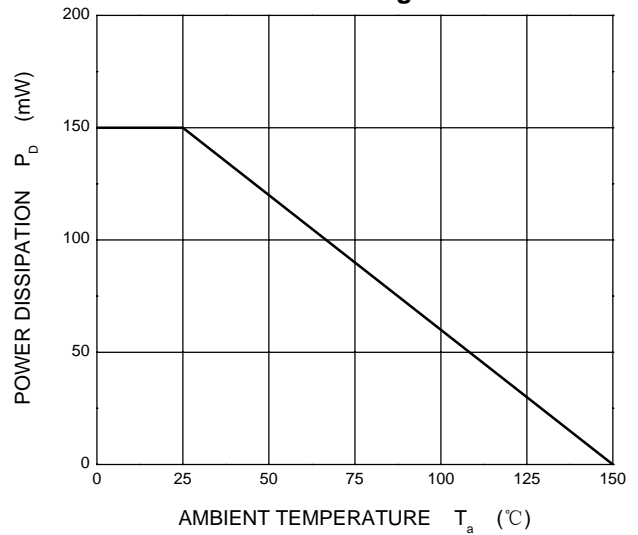
Reverse Characteristics



Capacitance Characteristics

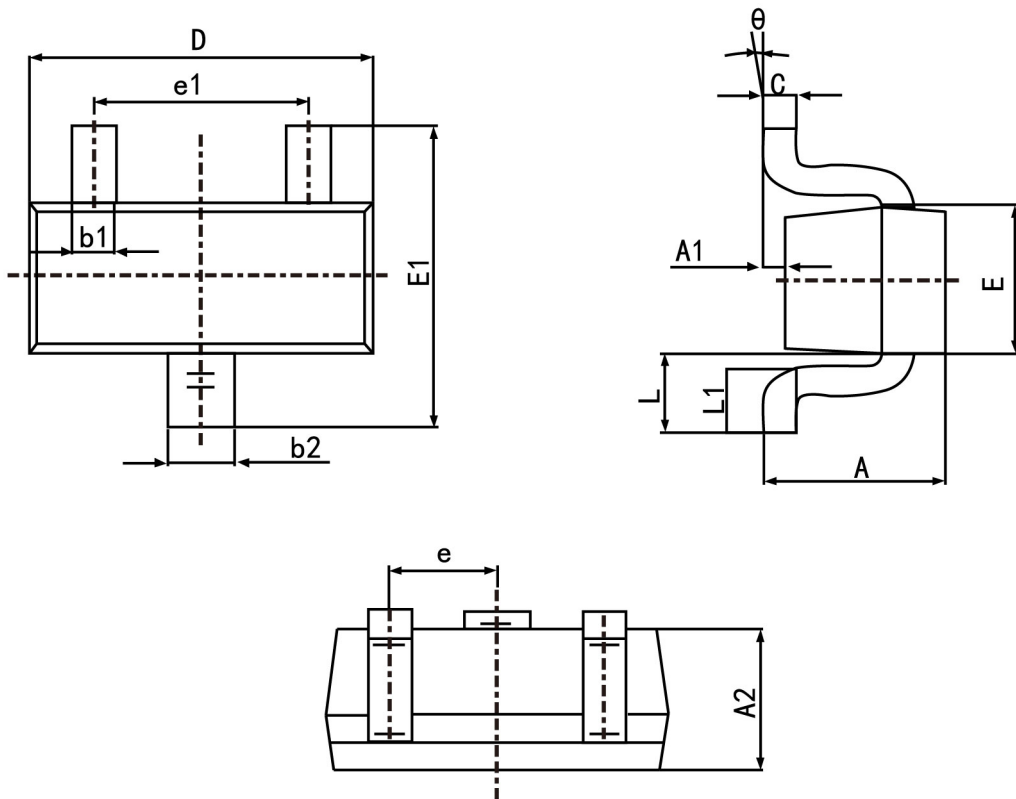


Power Derating Curve





SOT-523 PACKAGE OUTLINE



Symbol	Dimension in Millimeters	
	Min	Max
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b1	0.150	0.250
b2	0.250	0.350
c	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500	TYP.
e1	0.900	1.100
L	0.400 REF.	
L1	0.260	0.460
θ	0°	8°